

Silicon PNP transistor epitaxial type BP005

[Applications]

General purpose

[Feature]

Low collector saturation voltage $V_{CE(sat)} = -0.25V(\text{Max.})$ at $I_C = -100mA$, $I_B = -10mA$

[Absolute maximum ratings ($T_a=25C$)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-80	V
Collector-emitter voltage	VCEO	-80	V
Emitter-base voltage	VEBO	-4	V
Collector current	IC	-200	mA
Junction temperature	Tj	125	C
Storage temperature	Tstg	-55 to 125	C

[Electrical characteristics ($T_a=25C$)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	-80	-	-	V	$I_C = -100\mu A$, $I_E = 0A$
Collector-emitter breakdown voltage	BVCEO	-80	-	-	V	$I_C = -1mA$, $I_B = 0A$
Emitter-base breakdown voltage	BVEBO	-4	-	-	V	$I_E = -100\mu A$, $I_C = 0A$
Collector cutoff current	ICBO	-	-	-100	nA	$V_{CB} = -80V$
Collector cutoff current	ICEO	-	-	-100	nA	$V_{CE} = -60V$
DC current gain 1	hFE 1	100	-	-	-	$V_{CE} = -1V$, $I_C = -10mA$
DC current gain 2	hFE 2	100	-	-	-	$V_{CE} = -1V$, $I_C = -100mA$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	-0.25	V	$I_C = -100mA$, $I_B = -10mA$
Base-emitter on voltage	$V_{BE(on)}$	-	-	-1.2	V	$V_{CE} = -1V$, $I_C = -100mA$
Transition frequency	fT	50	-	-	MHz	$V_{CE} = -1V$, $I_E = 100mA$

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

